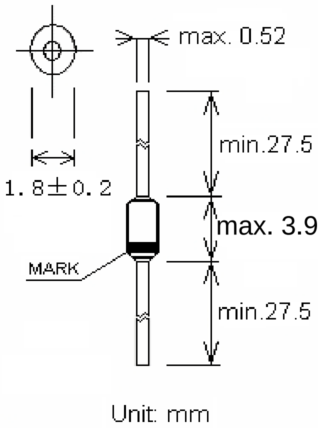
BZX55B-SERIES

ZENER DIODES

Zener Voltage:2.0-39V Peak Pulse Power:500mW

DO-35(GLASS)



FEATURE

- Low Reverse Leakage
- Low Zener Impedance
- Power Dissipation of 500mW
- High Stability and High Reliability

MECHANICAL DATA

Case: DO-35 Glass Case
Polarity: Color band denotes cathode end
Mounting Position: Any

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum Ratings & Thermal Characteristics (Ratings at 25℃ ambient temperature unless otherwise specified.)

Parameters	Symbol	Value	Unit
Power Dissipation	Pd	500 1)	mW
Operating junction temperature	Tj	175	℃
Storage temperature range	Ts	-55-+175	℃

1) Valid provided that leads are kept at ambient temperature at a distance of 8mm from case

ELECTRICAL CHARACTERISTICS (at T_A=25℃ unless otherwise noted)

TYPE	Zener Voltage			Reverse Carrent		Dynamic Resistance	
	Vz(V)		Test Condition	Ir(uA)	Test Condition	rd(Ω)	Test Condition
	Min.	Max.	Iz(mA)	Max.	Vr(V)	Max.	Iz(mA)
BZX55B 2V0	1.96	2.04	5.0	100	1.0	85	5.0
BZX55B 2V2	2.16	2.24	5.0	75	1.0	85	5.0
BZX55B 2V4	2.35	2.45	5.0	50	1.0	85	5.0
BZX55B 2V7	2.65	2.75	5.0	10	1.0	85	5.0
BZX55B 3V0	2.94	3.06	5.0	4	1.0	85	5.0
BZX55B 3V3	3.23	3.37	5.0	2	1.0	85	5.0
BZX55B 3V6	3.53	3.67	5.0	2	1.0	85	5.0
BZX55B 3V9	3.82	3.98	5.0	2	1.0	85	5.0
BZX55B 4V3	4.21	4.39	5.0	1	1.0	75	5.0
BZX55B 4V7	4.61	4.79	5.0	0.5	1.0	60	5.0
BZX55B 5V1	5.00	5.20	5.0	0.1	1.0	35	5.0
BZX55B 5V6	5.49	5.71	5.0	0.1	1.0	25	5.0
BZX55B6V2	6.08	6.32	5.0	0.1	2.0	10	5.0
BZX55B 6V8	6.66	6.94	5.0	0.1	3.0	8	5.0
BZX55B 7V5	7.35	7.65	5.0	0.1	5.0	7	5.0
BZX55B 8V2	8.04	8.36	5.0	0.1	6.2	7	5.0
BZX55B 9V1	8.92	9.28	5.0	0.1	6.8	10	5.0
BZX55B 10	9.80	10.20	5.0	0.1	7.5	15	5.0
BZX55B 11	10.78	11.12	5.0	0.1	8.2	20	5.0
BZX55B 12	11.76	12.24	5.0	0.1	9.1	20	5.0
BZX55B 13	12.74	13.26	5.0	0.1	10.0	26	5.0
BZX55B 15	14.70	15.30	5.0	0.1	11.0	30	5.0
BZX55B 16	15.68	16.32	5.0	0.1	12.0	40	5.0
BZX55B 18	17.64	18.36	5.0	0.1	13.0	50	5.0
BZX55B 20	19.60	20.40	5.0	0.1	15.0	55	5.0
BZX55B 22	21.56	22.44	5.0	0.1	16.0	55	5.0
BZX55B 24	23.52	24.48	5.0	0.1	18.0	80	5.0
BZX55B 27	26.46	27.54	5.0	0.1	20.0	80	5.0
BZX55B 30	29.40	36.60	5.0	0.1	22.0	80	5.0
BZX55B 33	32.34	33.66	5.0	0.1	24.0	80	5.0
BZX55B 36	35.28	36.72	5.0	0.1	27.0	80	5.0
BZX55B 39	38.22	39.78	2.5	0.1	30.0	90	2.5

Notes:

1) Tested with pulses tp = 20 ms.
2) Valid provided that leads are kept at ambient temperature at a distance of 8 mm from case
3) The BZX55-C0V8 is a silicon diode with operation in forward direction. Hence, the index of all parameters should be “F” instead of “Z”. Connect the cathode lead to the negative pole.
4) VF(Max)=1.20V@ IF=100mA

RATINGS AND CHARACTERISTIC CURVES BZX55B SERIES

Breakdown characteristics Tj = constant (pulsed)